

spin density in the crystallized silicon film; and
patterning the crystallized silicon film into an island after the
thermally annealing step.

E 1
2. (Three Times Amended) A method for producing a semiconductor
device, comprising the steps of:

irradiating a non-single crystalline silicon film with laser light to
crystallize the non-single crystalline silicon film;

thermally annealing the non-single crystalline silicon film in the
temperature range of 450-750°C [under a non-oxidizing atmosphere] to
decrease dangling bonds in the crystallized silicon film; and

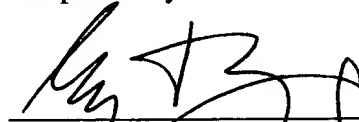
patterning the crystallized silicon film into an island after the
thermally annealing step.

REMARKS

Claims 1 and 2 have been amended to complete the scope of applicants'
protection.

Examination on the merits is requested.

Respectfully submitted,



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